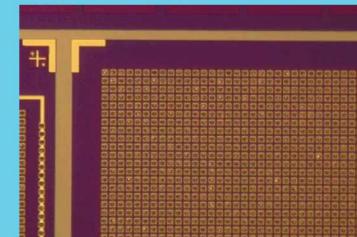
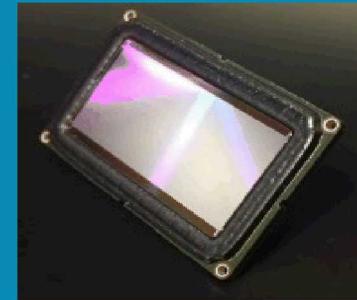


Q. Looker, A. P. Colombo, A. D. Edens, M. W. Kimmel, J. W. Stahoviak, M. O. Sanchez, L. D. Claus, M. G. Wood, G. A. Rochau, J. L. Porter



Outline

The Ultrafast X-Ray Imager program at Sandia National Laboratories

- 2-D x-ray imagers with ~nanosecond gate times designed and fabricated at SNL
- Fielded at Z Machine, NIF, Omega, SLAC, ...

Applications at Sandia's Z Machine

- Gated radiography
- Time-resolved spectroscopy
- Multi-frame x-ray imaging

Characterization Methods

- Temporal gate profiles
- Linearity of response
- Application-specific configuration testing

Sensor improvements

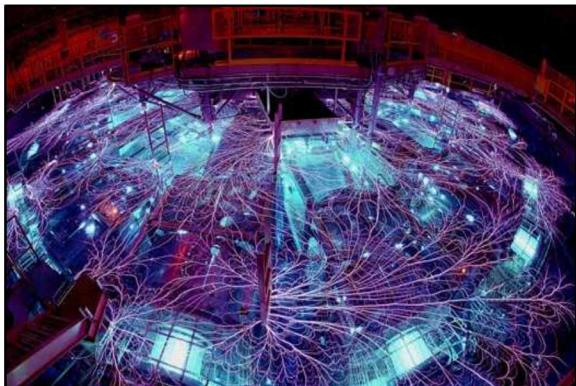
- ROIC improvements to reduce gate time, number of frames, ...
- Superlattice enhancement for soft x-rays, electrons
- Thicker Si detectors and GaAs detectors



The Ultrafast X-Ray Imager Program at Sandia National Laboratories



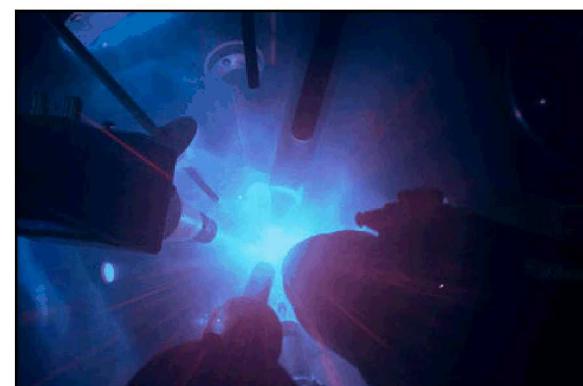
The UXI program at Sandia has created a new class of 2D, nanosecond-gated x-ray imagers



Z-Machine

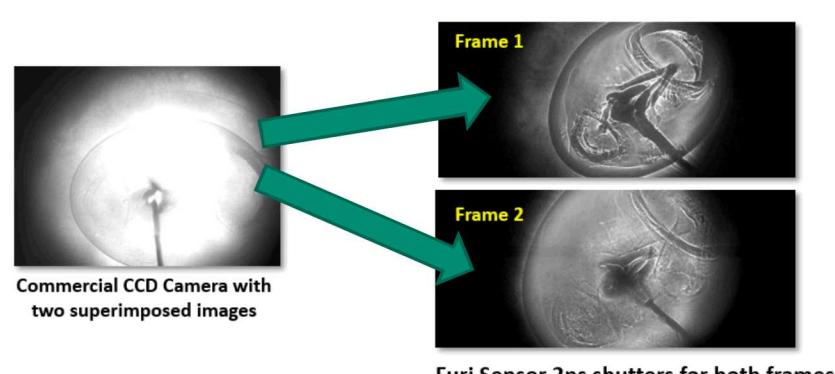


National Ignition Facility



Omega

- X-ray imaging is a valuable diagnostic for Inertial Confinement Fusion (ICF) and High Energy Density (HED) physics research
- Faster frame-rate reduces motion blur while multiple frames provide a temporal history of an evolving experiment
- Burst-mode CMOS imagers provide unique capability for multiple x-ray images on single line of sight with nanosecond gate times



Commercial CCD Camera with two superimposed images

Furi Sensor 2ns shutters for both frames

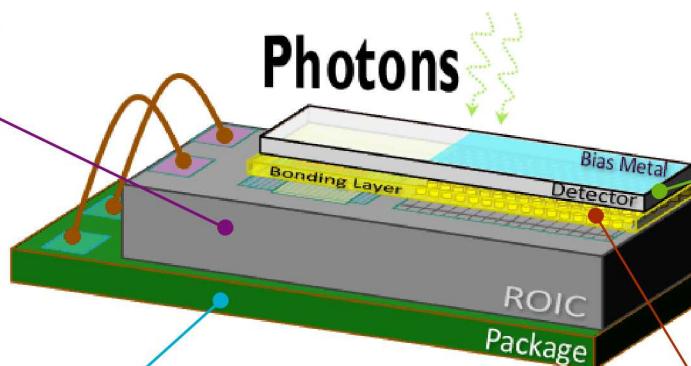
Many parts come together to become a hybrid CMOS UXI camera

Readout Integrated Circuit (ROIC)

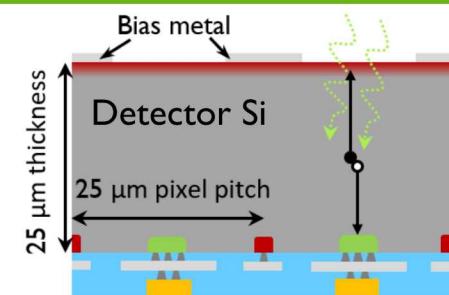


- Fabricated in SNL's 6" 350nm CMOS
- 1-2ns min shutter, 2-8 frames
- 1024x512 array of $25\mu\text{m} \times 25\mu\text{m}$ pixels
- Adjustable shutter timing

Photons



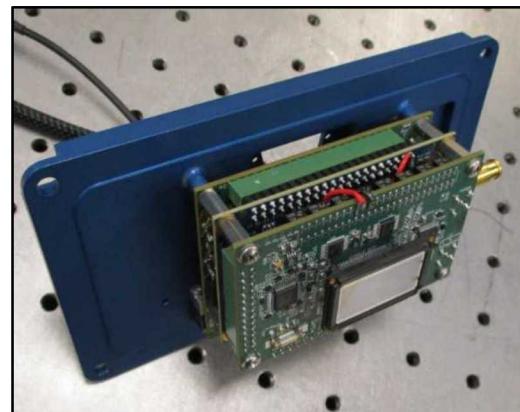
Detector Array



Package

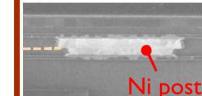


Hybrid CMOS Sensor



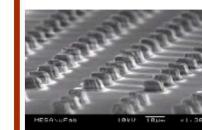
Integration

Direct Bond Interconnect (DBI)



- External supplier
- Wafer-to-wafer bond

Indium bump

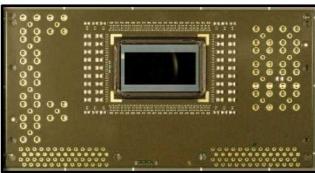


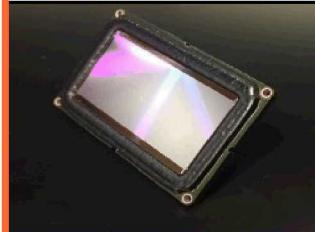
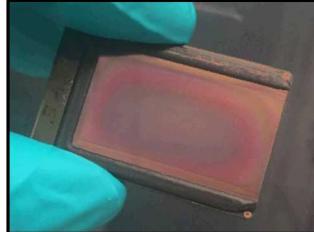
- Processing at Sandia
- Die-level processing

**UXI Camera System Development
for Application-Specific Needs**

Icarus is the state-of-the-art sensor in an advancing product line

In Use			In Test
	Furi	Hippogriff	Icarus
Year	FY14	FY15	FY16
Min Integration time	~1.5 ns	~2 ns	~1.5 ns
Frames	2	2 (full resolution) 4 or 8 (Row interlaced)	*4 (full resolution) *8 (L/R interlaced)
Tiling Option	No	No	No
CMOS Process	350 nm (SNL)	350 nm (SNL)	350 nm (SNL)
Pixels	448 x 1024	448 x 1024	512 x 1024
Pixel Size	25 μ m x 25 μ m	25 μ m x 25 μ m	25 μ m x 25 μ m
Capacitor Full Well	1.5 million e ⁻	1.5 million e ⁻	0.5 million e ⁻



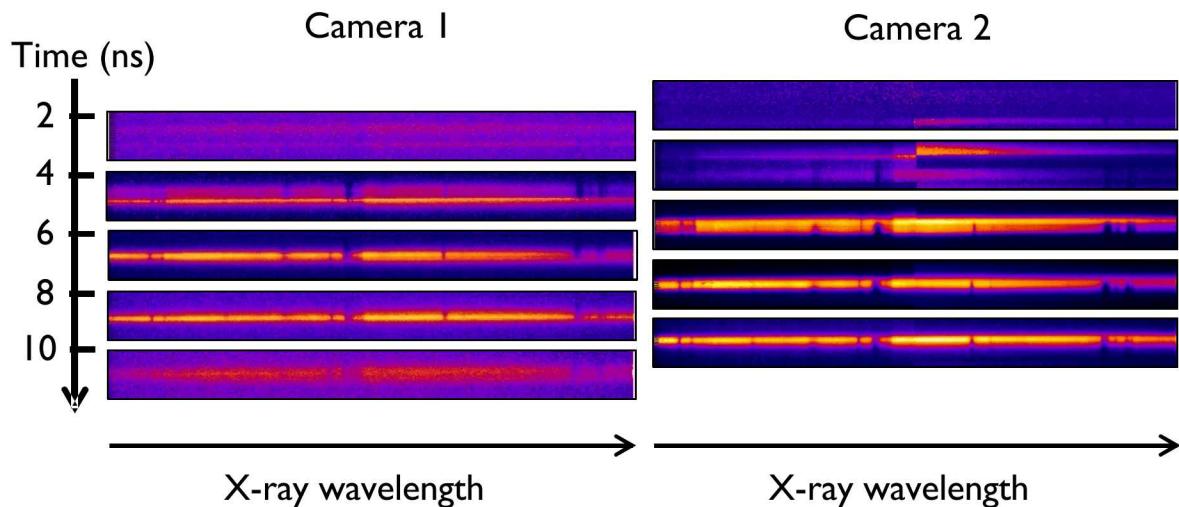
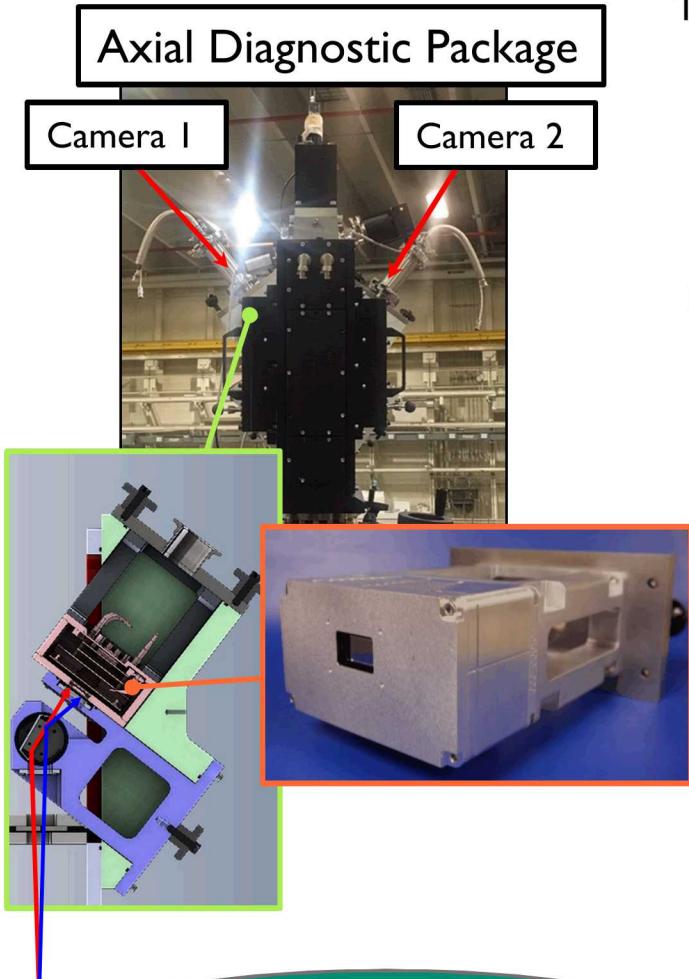





Applications at Sandia's Z Machine



Dual UXI cameras are now being used for 16-frame spectroscopy

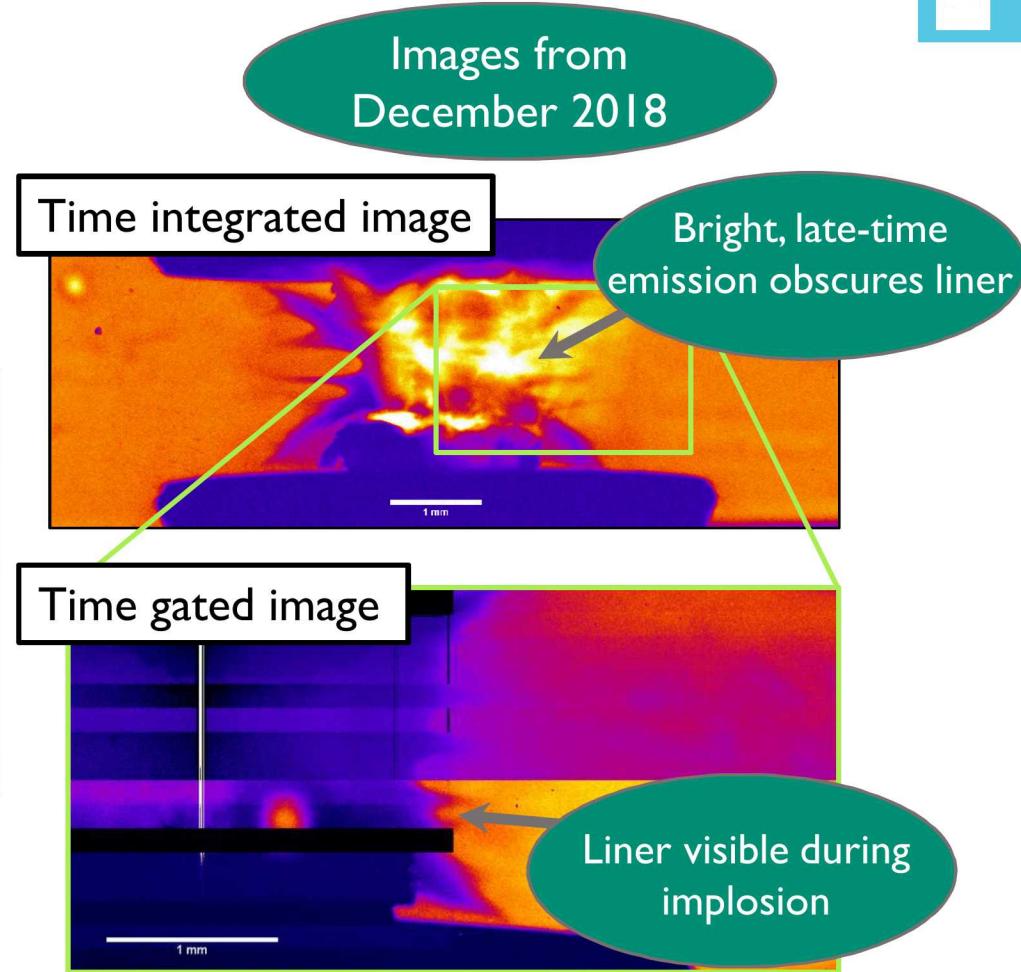
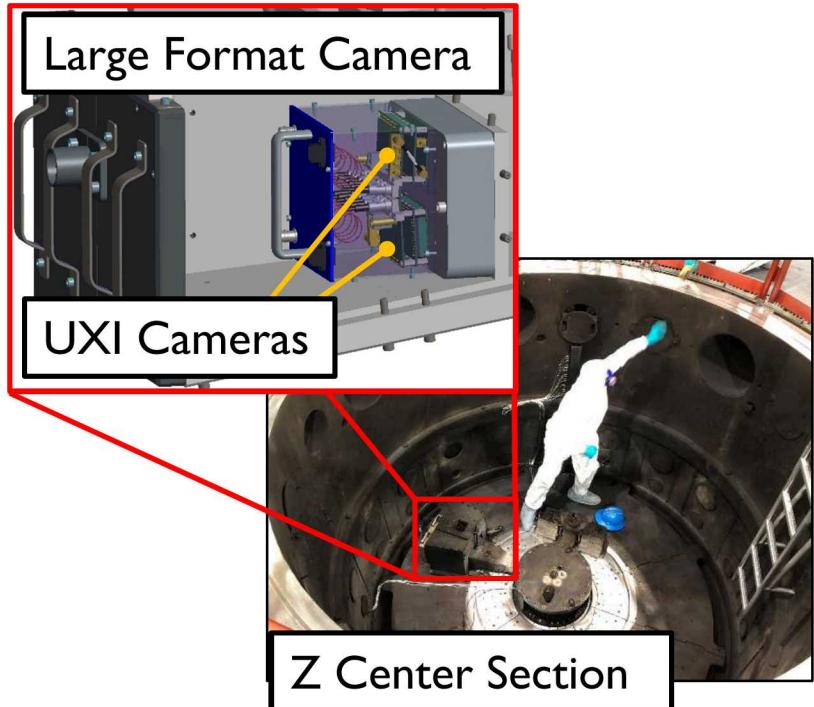


Temporal multiplexing
with 2 camera systems

- Two Icarus sensors employed with multiple slits each to create a 16-frame, time-resolved set of spectra

Crystal reflector
disperses x-ray energy in
one dimension

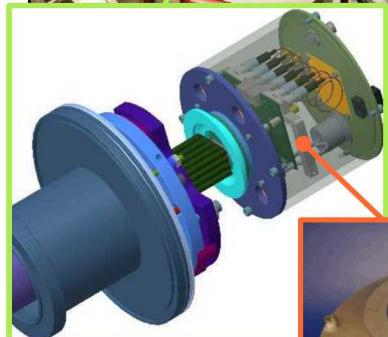
Gated radiography is making an impact on Z experiments



- Icarus sensor used to gate out late-time radiation, enabling higher contrast imaging of imploding liners
- Multiple frames possible on a single shot from a single line of sight
- Serious challenges in EMI, debris, shock, radiation tolerance

Time-resolved, multi-frame pinhole images are being used to diagnose laser preheat conditions

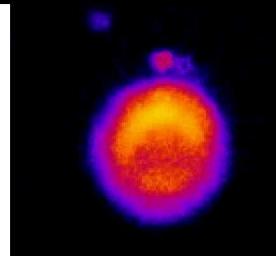
Z Final Optics Assembly



1 mm

Typical laser preheat with phase plate

Laser preheat with observed dust particles



Time series with color channels

Filter 1
Filter 2

Laser preheat with no phase plate

- Icarus sensor used in pinhole camera system to image MagLIF laser-induced plasma prior to stagnation
- Multiple images with two different filters

Time

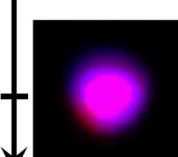
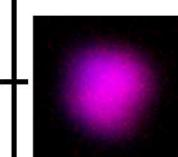
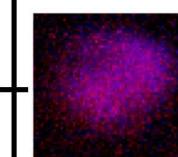
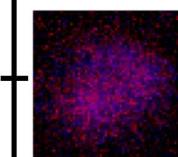
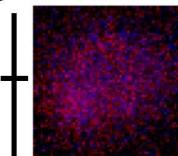
5 ns

10 ns

15 ns

20 ns

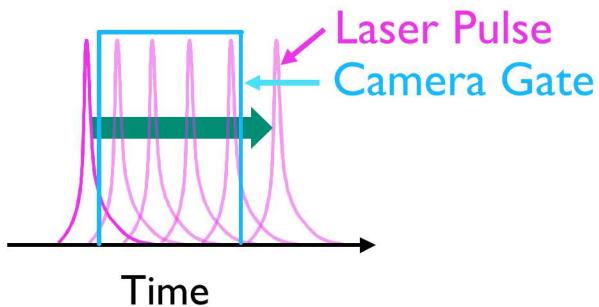
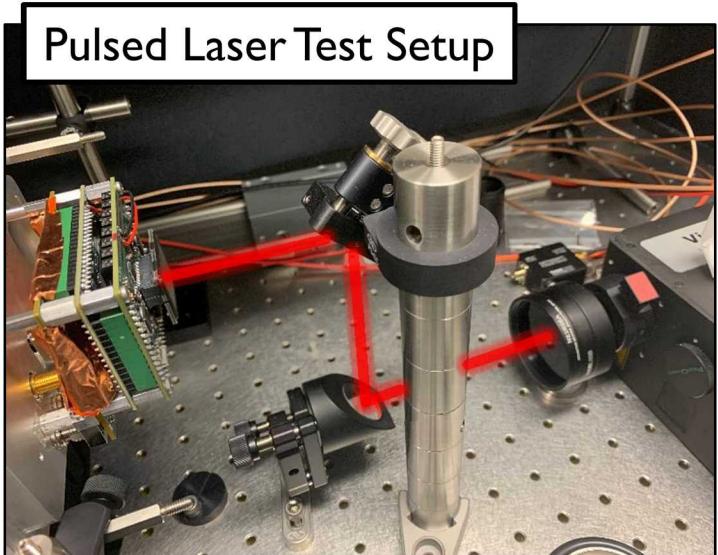
25 ns





Characterization Methods

The camera's temporal gate profile is characterized by sweeping laser pulses in time

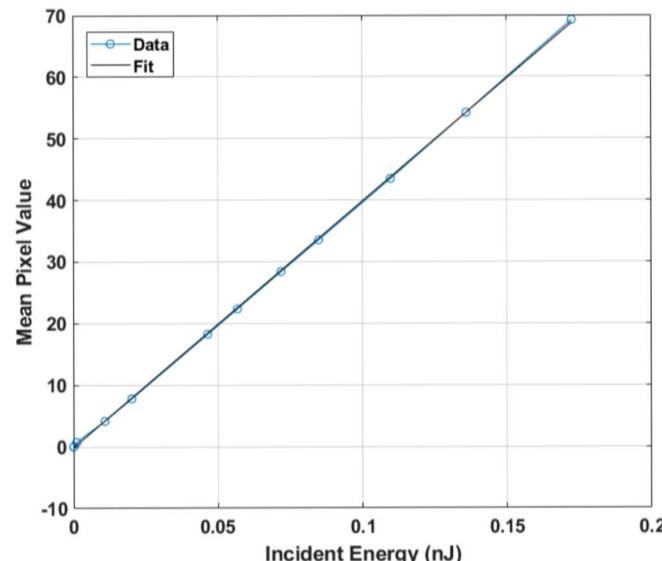
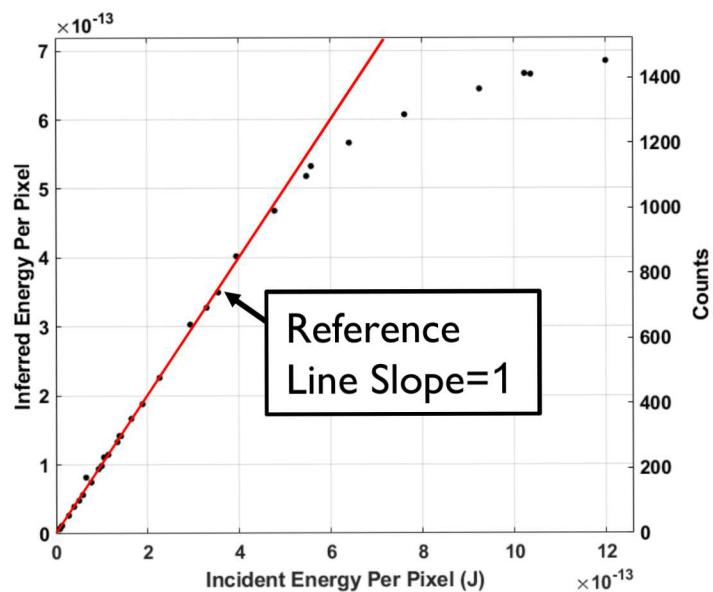
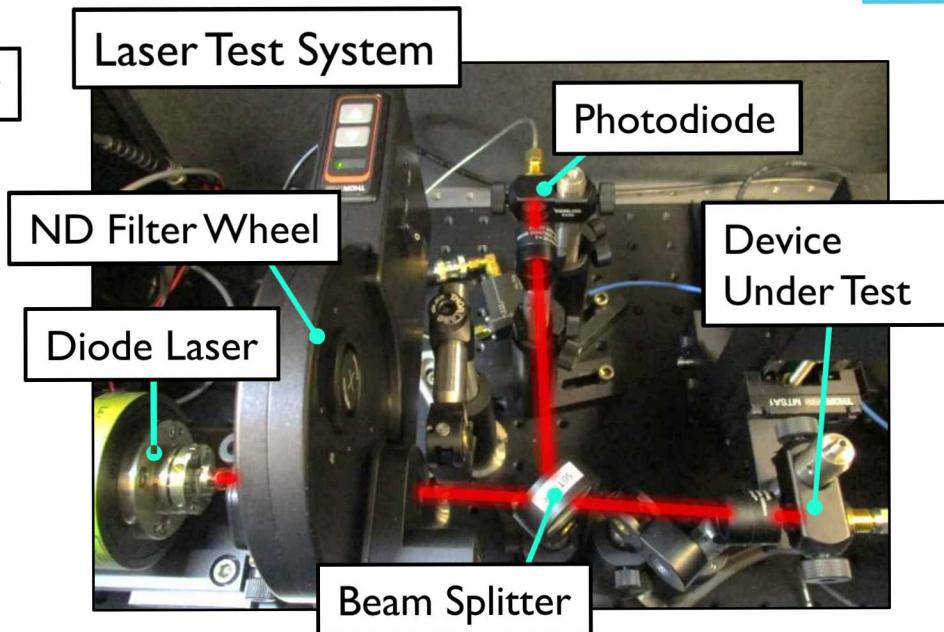
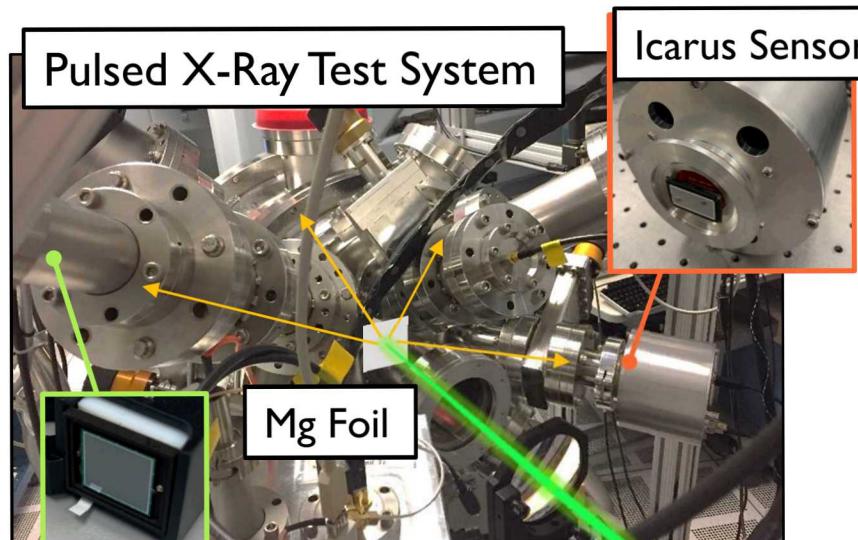


Example gate profile
scan with 2 ns exposure
time over 4 frames

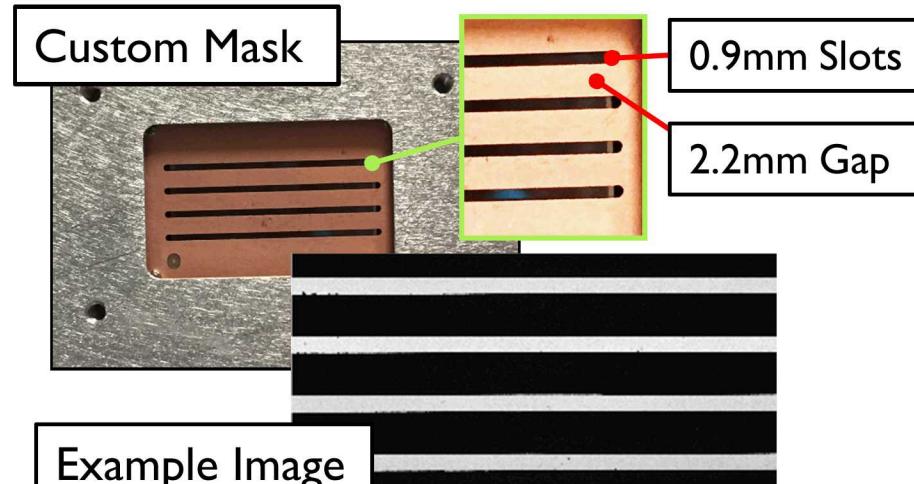
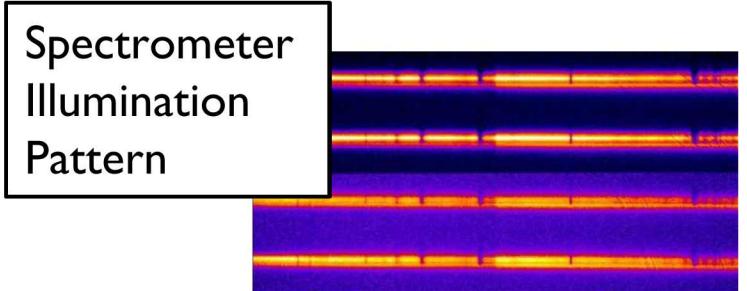
F0 F1 F2 F3

- Tabletop laser system allows rapid characterization of each sensor in a variety of timing modes

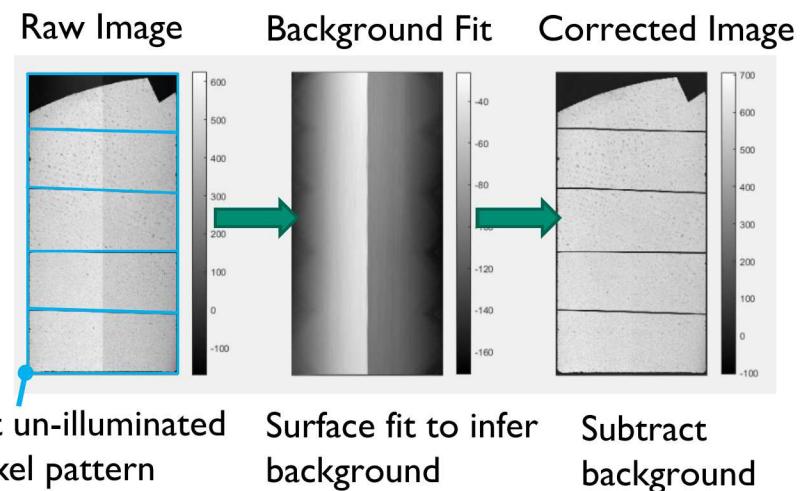
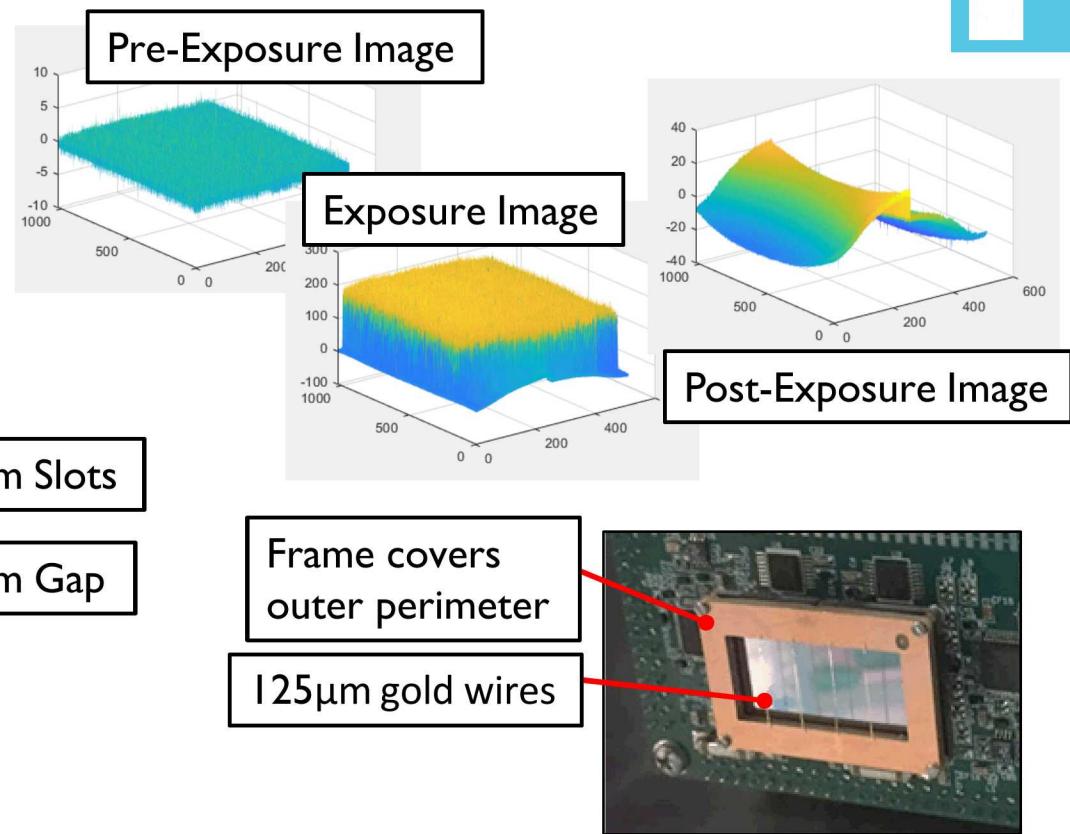
The camera's linearity and sensitivity are characterized with x-ray and laser illumination



Application-specific masks aid in characterizing background

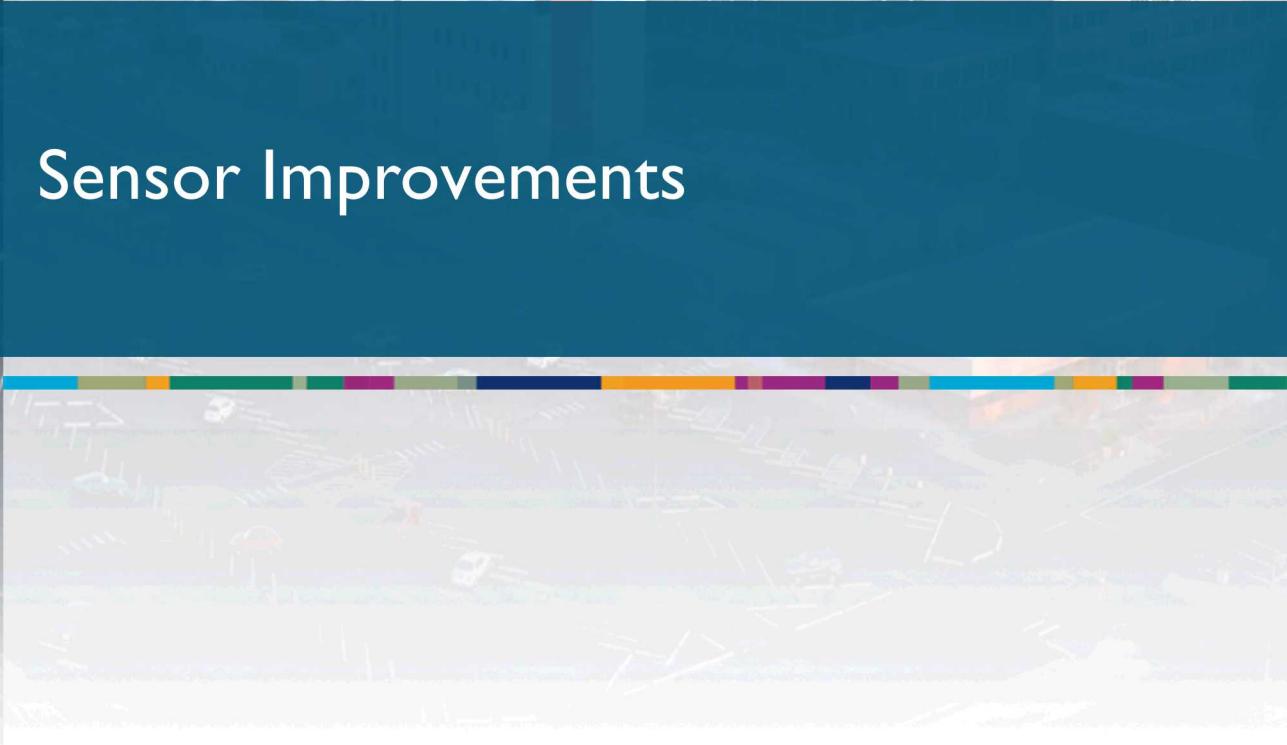


- Opacity spectrometer on Z machine utilizes 4-slit pattern, sensitive to changes in intensity along spectrum
- Custom mask mimics illumination pattern with uniform illumination to examine sensor response



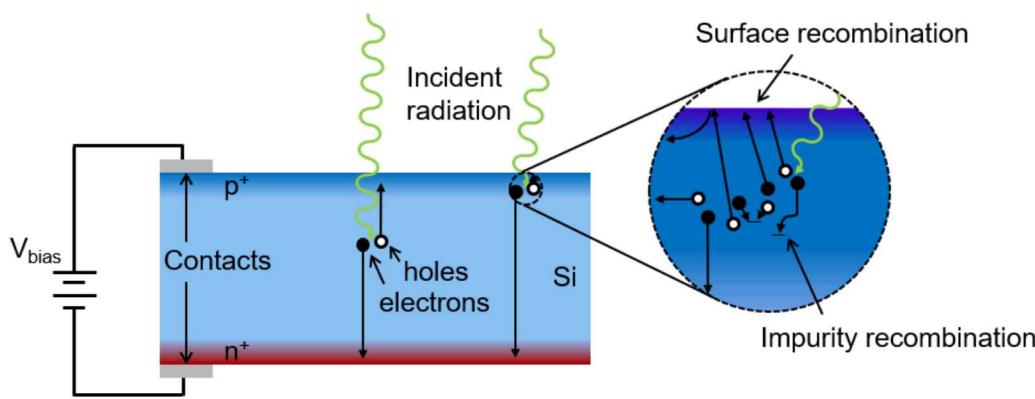


Sensor Improvements

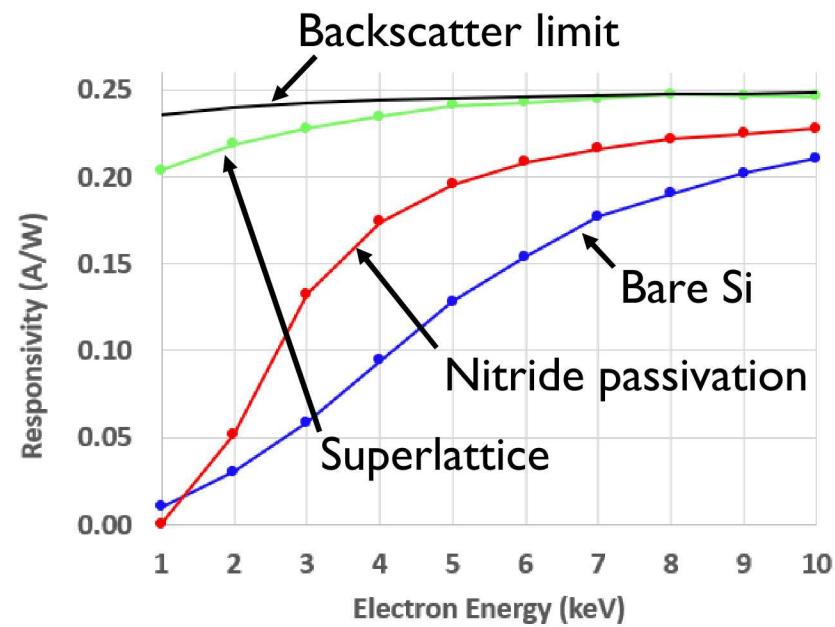
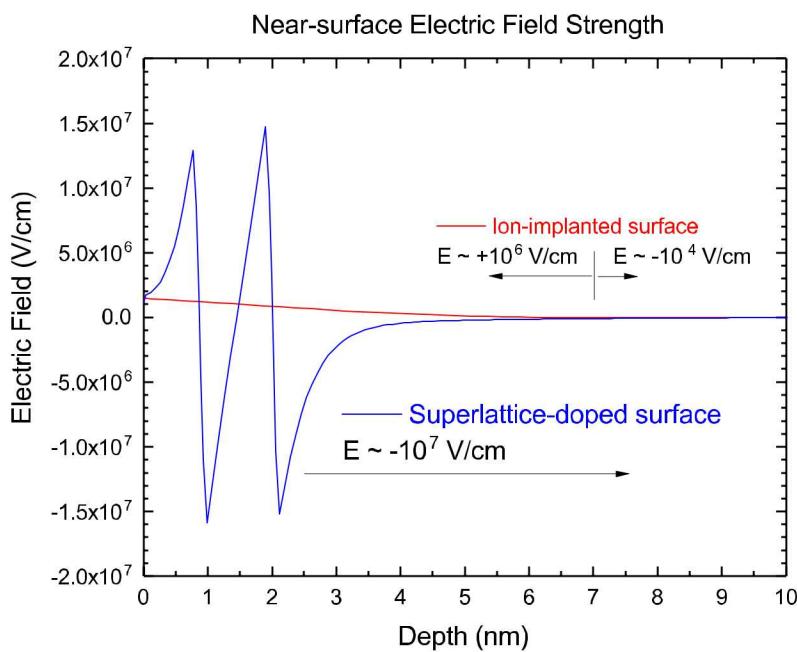


ROIC performance continues to offer improvements in speed, robustness, and timing flexibility

The addition of a quantum superlattice improves responsivity for shallowly absorbed particles

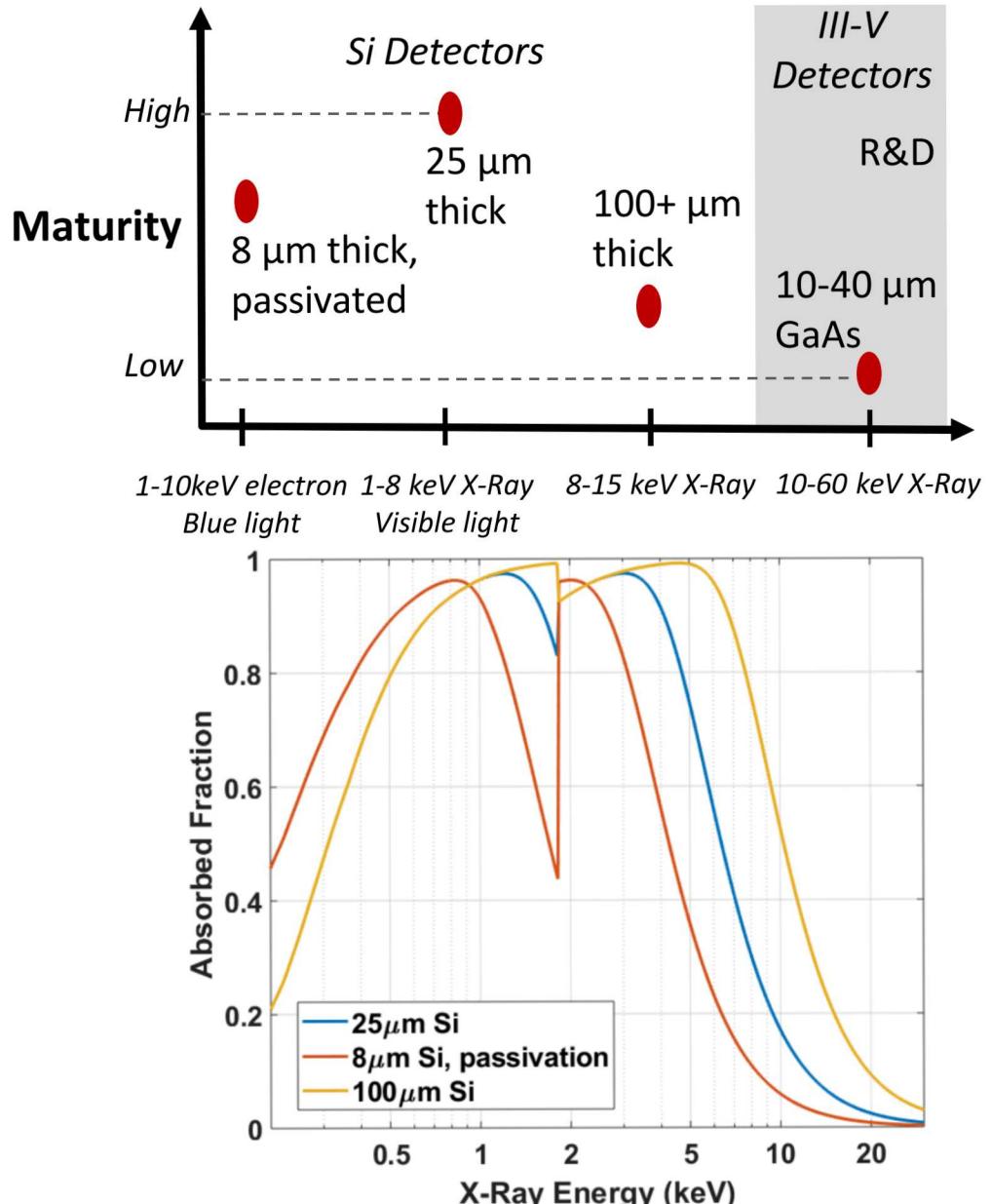


- For electrons, soft x-rays, and near-UV light, dead layer dictates detector sensitivity
- Quantum superlattice-enhanced detectors developed in partnership with NASA JPL demonstrated substantial increase in sensitivity



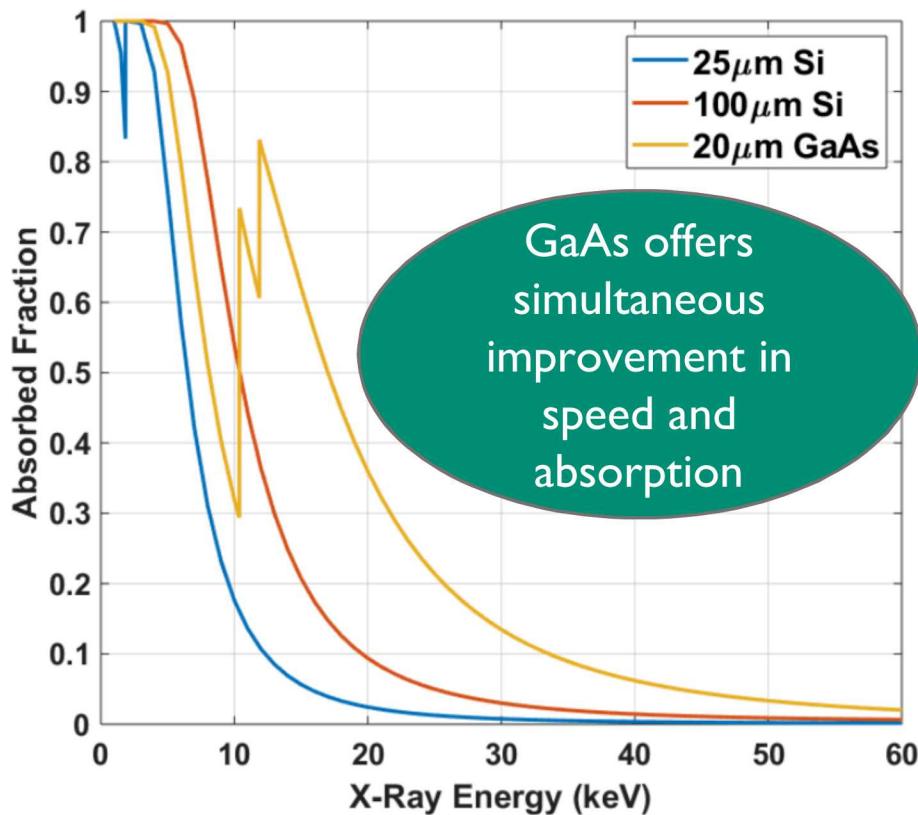
Sensor thickness can be tailored to meet application needs

- Most deployed detectors 25 μm Si
 - Mature fabrication and integration
 - $\sim 700\text{ps}$ impulse response
- 8 μm Si deployed on a limited basis with passivation
 - Mature sensor fabrication
 - Passivation adds integration complexity
 - $\sim 400\text{ps}$ impulse response
- 100 μm Si being developed for greater hard x-ray sensitivity
 - Only effective up to $\sim 15\text{ keV}$ x-ray energy
 - Add integration complexity
 - $\sim 3\text{ns}$ impulse response

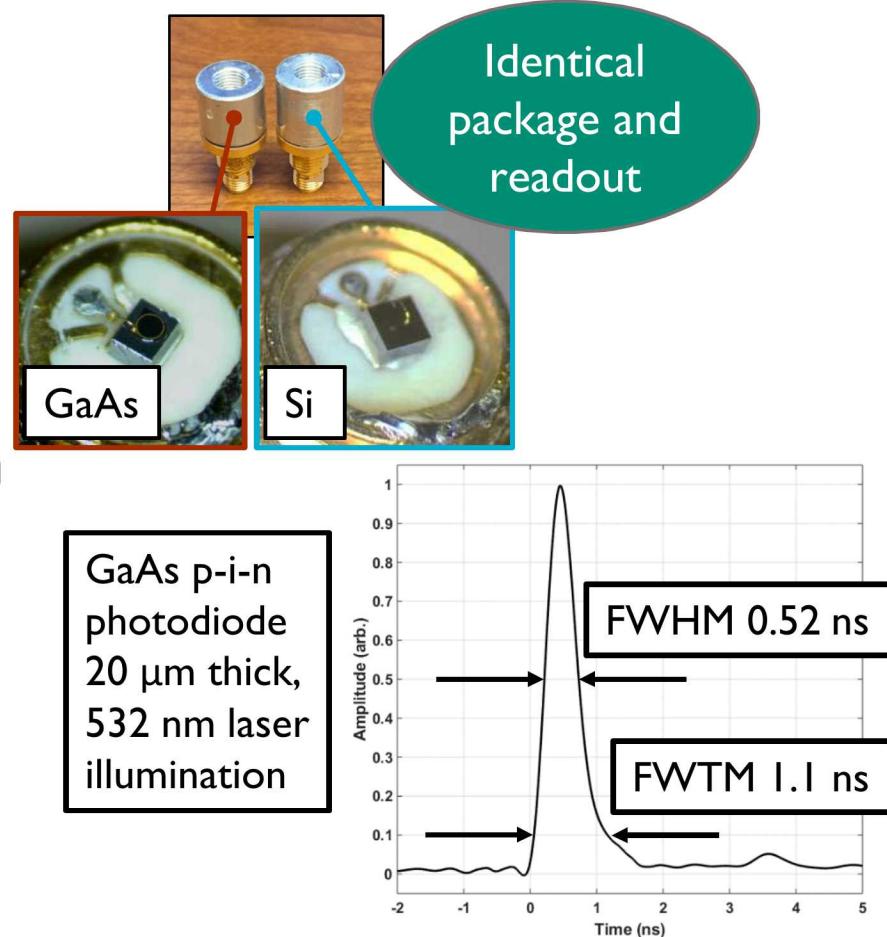


Sandia has developed fast GaAs photodiodes to improve hard x-ray sensitivity

- Si hard x-ray response limited, temporal response hampered by thick detectors
- Photoelectric absorption $\sim Z^4$

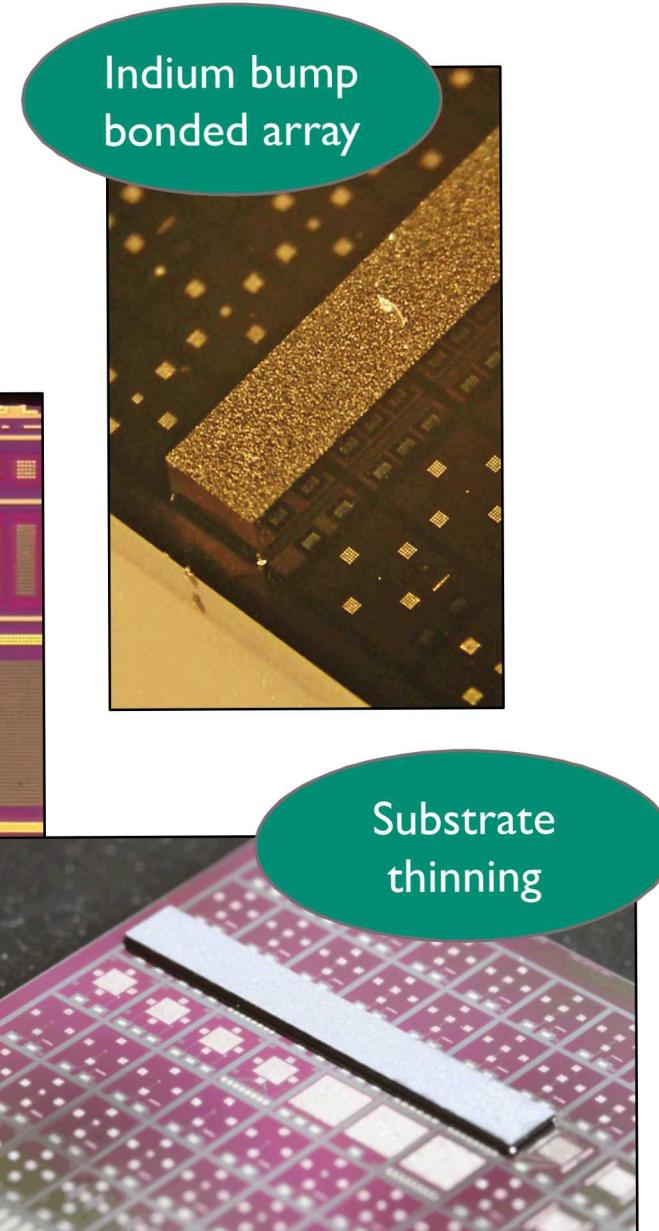
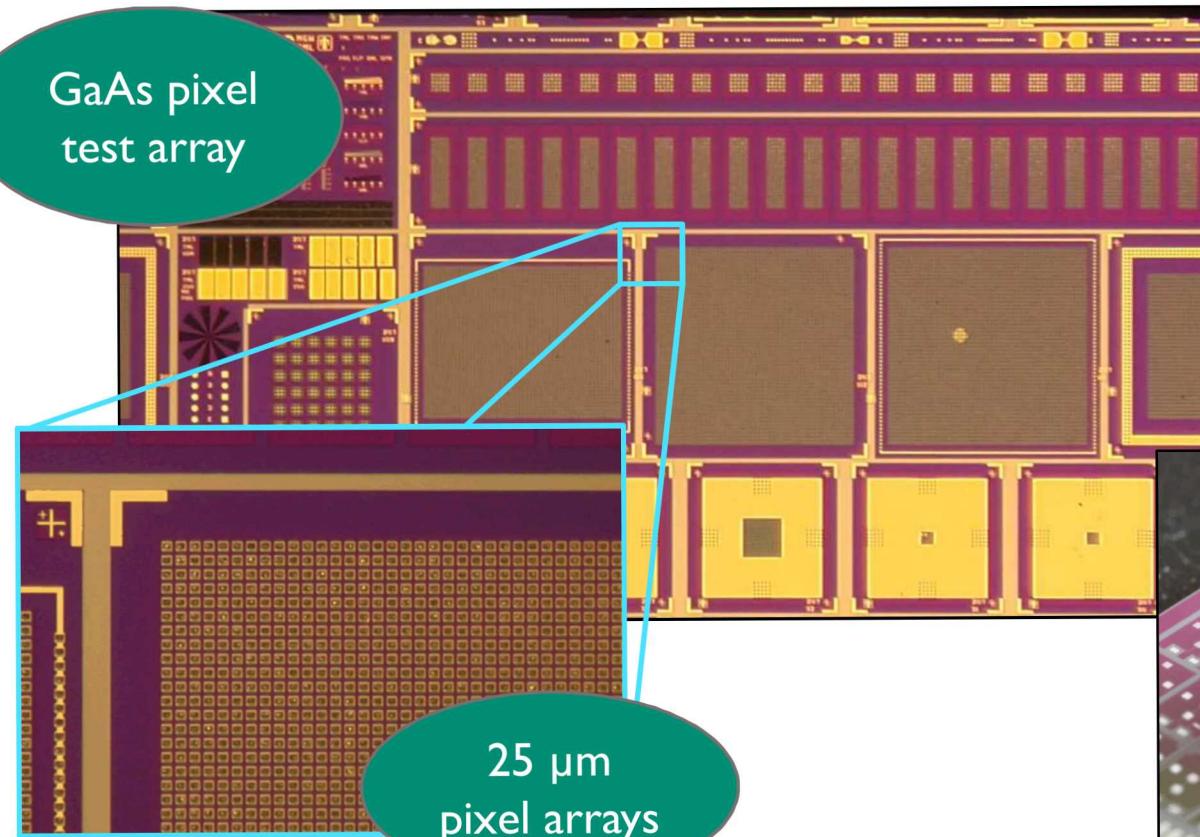


- Superior hard x-ray absorption and sub-nanosecond response demonstrated in frontside-illuminated GaAs detectors

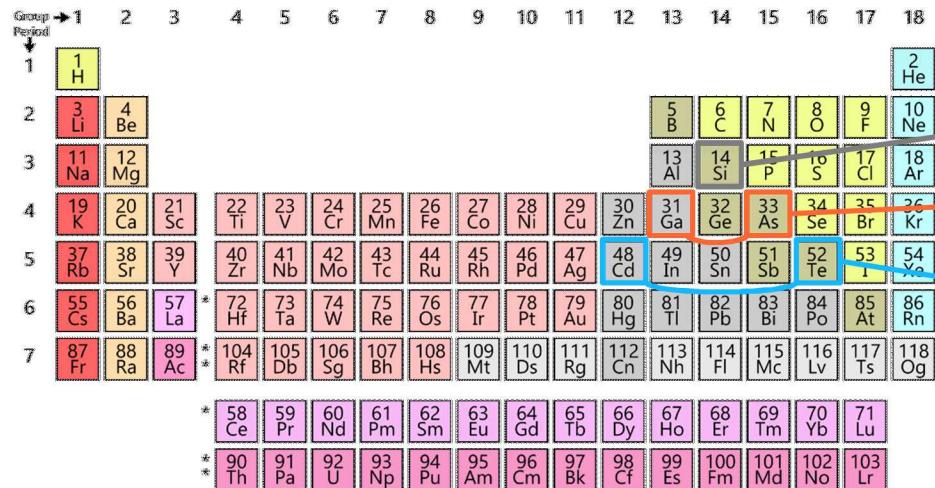


Backside-illuminated GaAs pixel arrays are being developed for hCMOS detectors

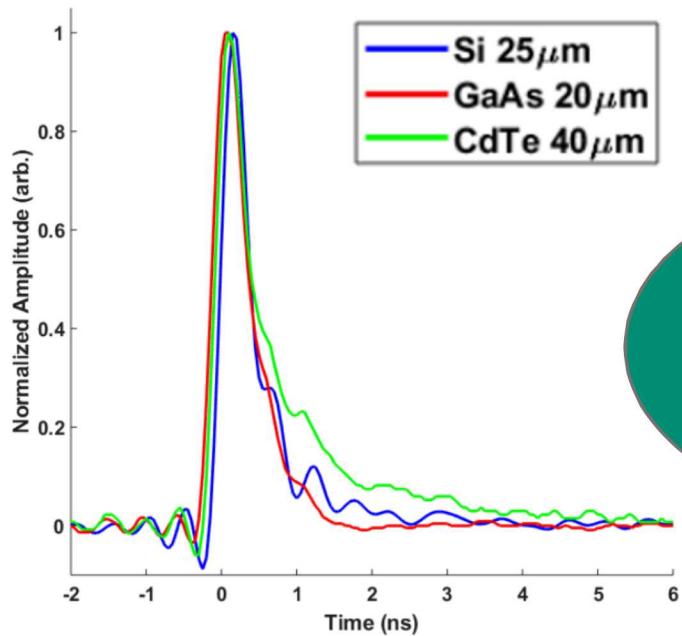
- Process changes required for hybrid CMOS compatibility
- First bonded test arrays complete
- 0.5 Mpix Icarus/Daedalus arrays available next year



Other detector materials show promise for hard x-ray detectors



Material Investigated	Notes
Si	Mature fabrication, low Z
GaAs	Demonstrated fast detectors
CdTe	Demonstrated fast detectors
CdZnTe	Cannot obtain small detectors
GaN	Background doping too high
AlSb	Leakage current too high



Detector pulse shapes obtained with Advanced Photon Source white beam

Nanosecond-gated imagers are expanding possibilities in ICF and HED Physics

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Please see poster 3P04 for more exciting applications of UXI camera systems

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